Ref #	Hits	Search Query	DBs	Default Operat or	Plural s	Time Stamp
L2	50	self near3 limiting near3 (oxidizing oxidation oxidized oxidization) with oxide	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/25 06:35
L3	61	self near3 limiting near5 (oxidizing oxidation oxidized oxidization) with oxide	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/25 06:35
L4	66	self near3 limiting near6 (oxidizing oxidation oxidized oxidization) with oxide	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/25 06:35
L5	95	self near3 limiting with (oxidizing oxidation oxidized oxidization) with oxide	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/25 06:36
L6	95	self with limiting with (oxidizing oxidation oxidized oxidization) with oxide	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/25 06:36
S58	1	10/630969	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:16
S59	7144	oxide with low adj pressure	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:17
S60	476	S59 and (oxide low adj pressure) with torr	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:17
S61	478	S59 and (oxide low adj pressure) with (torr pascal)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:18
S62	479	S59 and (oxide low adj pressure) with (torr pascal atmosphereic)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:18

S63	370	S62 and (oxide with (thick thickness thicker))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:19
S64	146	S63 and ((oxide thick thickness thicker) with angstrom)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:20
S65	74	S64 and (oxide with (oxygen 'o2' oxygen adj containing))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:24
S66	206	oxide with self adj limiting near3 oxid\$4	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:55
S67	50	oxide with self adj limiting near3 (oxidizing oxidation oxidized oxidization)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:56
S68	163	self adj limiting near3 (oxidizing oxidation oxidized oxidization)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/24 17:57
S69	50	self adj limiting near3 (oxidizing oxidation oxidized oxidization) with oxide	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/01/25 06:35

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	U	1	Document ID	Issue Dat	Page	Title	Current O	Current X Retrieva
1	ה	П	US 20050059259 .	A 2005031	18	Interfacial oxidation process for high-k gate dielectric proce	438/765	257/E21.2
2	D	E	US 20050026459	A 2005020	16	Method of forming uniform ultra-thin oxynitride layers	438/786	257/E21.2
3	Ę	o	US 20050026453	A 2005020	15	Formation of ultra-thin oxide layers by self-limiting interfac	438/778	257/E21.2
4	С	r l	US 20040229447	A 2004111	26	Process for producing luminescent silicon nanoparticles	438/507	
5	r,	r. [1	US 20040182915.	A 2004092	16	Structure and method for bonding to copper interconnect st	228/220	228/215;
6	Б	n	US 20040087079	A 2004050	6	METHOD OF FORMING A NITRIDE GATE DIELECTRI	438/216	257/E21.1
7	C	Б	US 20030180556	A 2003092	5	Corrosive-resistant coating over aluminum substrates for us	428/472.2	427/255.28
8	Г	6	US 20030060057	A 2003032	10	Method of forming ultrathin oxide layer	438/770	257/E21.1
9	r	г.	US 20030052358 .	A 2003032	12	Method of improved high K dielectric - polysilicon interfac	257/310	257/309;
10	С	r l	US 20030049942	A 2003031	9	Low temperature gate stack	438/778	257/E21.1
11	С	6	US 20030042526	A 2003030	12	Method of improved high K dielectric-polysilicon interface	257/309	257/E21.0
12	С	П	US 20030032304	A 2003021	14	Process for the electrochemical oxidation of a semiconduct	438/770	257/E21.2
13	Γ,	r	US 20010031562	A 2001101	10	Method of forming ultrathin oxide layer	438/770	257/E21.1
14	Ľ	r l	US 20010017421	A 2001083	3	Semiconductor element with metal layer	257/767	257/E21.5
15	C	Б	US 6974779 B2	2005121	17	Interfacial oxidation process for high-k gate dielectric proce	438/769	438/770
16	[]	Б	US 6863926 B2	2005030	5	Corrosive-resistant coating over aluminum substrates for us	427/250	427/249.15
17	Г	г	US 6806145 B2	2004101	11	Low temperature method of forming a gate stack with a hig	438/287	257/E21.1
18	Б		US 6794314 B2	2004092	11	Method of forming ultrathin oxide layer	438/778	257/E21.1
19	П	c	US 6727134 B1	2004042	6	Method of forming a nitride gate dielectric layer for advanc	438/216	257/E21.1
30			116 5220080 <b>D</b> J	5003020	1.2	Dragons for the electrochemical axidation of a germinard est.	A20/770	257.0021.2.
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	U	1	Document ID	Issue Dat Page	The state of the s	1	Current X Retrieva
20	г	Б	US 6559069 B2	2003050 13	Process for the electrochemical oxidation of a semiconduct	438/770	257/E21.2
21	r	Г	US 6492283 B2	2002121 11	Method of forming ultrathin oxide layer	438/770	257/E21.1
22	Б	С	US 6444592 B1	2002090 6	Interfacial oxidation process for high-k gate dielectric proce	438/770	257/E21.2
23	Б	П	US 6417564 B2	2002070 3	Semiconductor element with metal layer	257/740	257/763;
24	г	Г	US 6329722 B1	2001121 7	Bonding pads for integrated circuits having copper intercon	257/786	257/690;
25	E	C	US 6197641 B1	2001030 17	Process for fabricating vertical transistors	438/268	257/E21.4
26	Б	Г	US 6165914 A	2000122 5	Method for fabricating semiconductor devices with thick hi	438/787	257/E21.2
27	Б	Б	US 6144071 A	2000110 18	Ultrathin silicon nitride containing sidewall spacers for imp	257/344	257/384;
28	г	Г	US 6103595 A	2000081 6	Assisted local oxidation of silicon	438/431	257/E21.5
29	ō	Б	US 6063665 A	2000051 6	Method for silicon surface control for shallow junction for	438/260	257/E21.3
30	n	С	US 5961791 A	1999100 11	Process for fabricating a semiconductor device	204/192.1	204/192.15
31	E	П	US 5916378 A	1999062 10	Method of reducing metal contamination during semicondu	148/243	148/275;
32	r	r.	US 5804910 A	1998090 7	Field emission displays with low function emitters and met	313/310	
33	E.	Б	US 5661073 A	1997082 6	Method for forming field oxide having uniform thickness	438/431	257/E21.5
34	Ľ.	Г	US 5589422 A	1996123 16	Controlled, gas phase process for removal of trace metal co	438/476	134/1.3;
35	П	Г	US 5359216 A	1994102 9	DRAM process with improved polysilicon-to-polysilicon c	257/306	257/297;
36	г	П	US 5334281 A	1994080 7	Method of forming thin silicon mesas having uniform thick	438/404	1 48/DIG.5
37	C	r	US RE34535 E	1994020 9	Floating gate memory with improved dielectric	365/185.0	257/319;
38	r:	b	US 5244825 A	1993091 8	DRAM process with improved poly-to-poly capacitor	438/241	257/E27.0
30000			TIC \$104910 A	<u>"i'oosovi"i'3"-</u>	Enhancion of internal wedislotein for EDD () M. related tooks	120/503	Joso@21.2.J
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32	г	r. US	5 5804910 A	1998090	7	Field emission displays with low function emitters and met	313/310		
33	٢	r US	5661073 A	1997082	6	Method for forming field oxide having uniform thickness	438/431	257/E21.5	
34	г	r US	5 5589422 A	1996123	16	Controlled, gas phase process for removal of trace metal co	438/476	134/1.3;	
35	Б	r. US	5359216 A	1994102	9	DRAM process with improved polysilicon-to-polysilicon c	257/306	257/297;	
86	Г	r US	5334281 A	1994080	7	Method of forming thin silicon mesas having uniform thick	438/404	148/DIG.5	
37	E	r US	RE34535 E	1994020	9	Floating gate memory with improved dielectric	365/185.0	257/319;	
8	Г	r US	5244825 A	1993091	8	DRAM process with improved poly-to-poly capacitor	438/241	257/E27.0	
9	Е	r US	5104819 A	1992041	13	Fabrication of interpoly dieletric for EPROM-related techn	438/593	257/E21.2	
0.	г	r US	5098192 A	1992032	10	DRAM with improved poly-to-poly capacitor	257/306	257/760;	
11	г	r US	4949154 A	1990081	11	Thin dielectrics over polysilicon	257/311	257/371;	
12	Г	r US	4922312 A	1990050	8	DRAM process with improved polysilicon-to-polysilicon c	257/297	257/300;	
3	Г	r US	4697330 A	1987100	10	Floating gate memory process with improved dielectric	438/261	257/E21.6	
14	г	r US	4656729 A	1987041	11	Dual electron injection structure and process with self-limit	438/261	257/316;	
15	Г	r US	3 4613956 A	1986092	8	Floating gate memory with improved dielectric	365/185.0	257/315;	
16	P.	r US	3 4577390 A	1986032	11	Fabrication of polysilicon to polysilicon capacitors with a c	438/396	257/371;	
17	P.	r US	3 4405659 A	1983092	9	Method for producing columnar grain ceramic thermal barri	427/248.1	427/250;	
18	P	пUS	S 4401697 A	1983083	10	Method for producing columnar grain ceramic thermal barri	427/250	204/192.15	
9	P.	r. US	3 4321311 A	1982032	9	Columnar grain ceramic thermal barrier coatings	428/623	428/629;	
0	P	r W	O 2005013348 A	2005021		FORMATION OF ULTRA-THIN OXIDE AND OXYNITRI		257/E21.2	
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